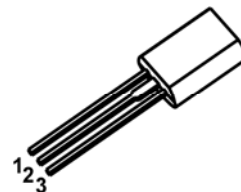


TO-92MOD Plastic-Encapsulate Transistors

2SB560 TRANSISTOR (PNP)

TO-92MOD

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



FEATURES

- High Reverse Voltage
- Low Saturation Voltage
- Suitable Universal AF Power Amplifier Use

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-0.7	A
P _c	Collector Power Dissipation	900	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10 uA, I _E =0	-100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1 mA, I _B =0	-80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10 uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -20 V, I _E =0			-1	μ A
Collector cut-off current	I _{EBO}	V _{EB} = -4V, I _B =0			-1	μ A
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _C = -50mA	60		560	
	h _{FE(2)}	V _{CE} = -5V, I _C = -500mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B = -50mA		-0.3	-0.8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B = -50mA		-0.85	-1.2	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA		100		MHz
Out capacitance	Cob	V _{CB} = -10 V, f=1MHz		15		pF

CLASSIFICATION OF h_{FE(1)}

Rank	D	E	F	G
Range	60 - 120	100 - 200	160 - 320	280 - 560